HALOGEN

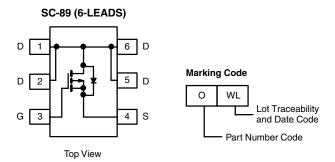
FREE





P-Channel 1.8 V (G-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
- 12	0.165 at V _{GS} = - 4.5 V	- 0.95		
	0.220 at V _{GS} = - 2.5 V	- 0.82		
	0.280 at V _{GS} = - 1.8 V	- 0.67		



Ordering Information: Si1039X-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Low Threshold
- Smallest LITTLE FOOT[®] Package: 1.6 mm x 1.6 mm
- · Low 0.6 mm Profile
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- · Cell Phones and Pagers
 - Load Switch

ABSOLUTE MAXIMUM RATINGS	(T _A = 25 °C, unle	ess otherwise	noted)			
Parameter		Symbol	5 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 12		V	
Gate-Source Voltage		V _{GS}	± 8			
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	- I _D	- 0.95	- 0.87	۸	
	T _A = 70 °C		- 0.76	- 0.69		
Pulsed Drain Current		I _{DM}	- 4		Α	
Continuous Diode Current (Diode Conduction) ^a		I _S	- 0.18	- 0.14	ı	
Maximum Power Dissipation ^a	T _A = 25 °C	- P _D	0.21	0.17	W	
	T _A = 70 °C	ı D	0.13	0.10	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maniana Institut to Ambienta	t ≤ 5 s	- R _{thJA}	500	600	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		600	720	C/VV	

Notes:

a. Surface mounted on 1" x 1" FR4 board with minimum copper.

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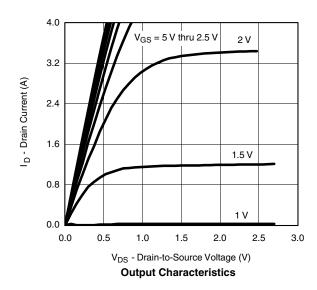
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	- 0.45			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = -12 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	μΑ	
	I _{DSS}	V _{DS} = - 12 V, V _{GS} = 0 V, T _J = 70 °C			- 5		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 4.5 V	- 4			Α	
Drain-Source On-State Resistance ^a		$V_{GS} = -4.5 \text{ V}, I_D = -0.87 \text{ A}$		0.140	0.165		
	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -0.75 \text{ A}$		0.180	0.220	Ω	
		$V_{GS} = -1.8 \text{ V}, I_D = -0.2 \text{ A}$		0.230	0.280		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 0.87 A		3.5		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = -0.14 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.78	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			3.8	6		
Gate-Source Charge	Q _{gs}	$V_{DS} = -6 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -0.87 \text{ A}$		0.7		nC	
Gate-Drain Charge	Q _{gd}			0.8		1	
Turn-On Delay Time	t _{d(on)}			15	30		
Rise Time	t _r	V_{DD} = - 6 V, R_L = 12 Ω		20	40		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 0.5 A, $V_{GEN}=$ - 4.5 V, $R_g=$ 6 Ω		30	60	ns	
Fall Time	t _f			16	30		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 0.14 A, dI/dt = 100 A/μs		20	40		

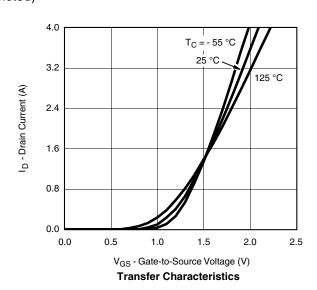
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

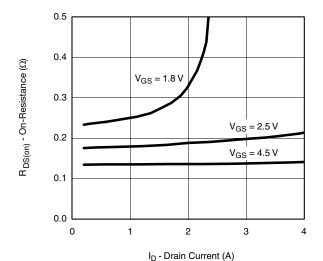




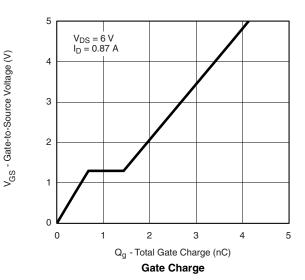


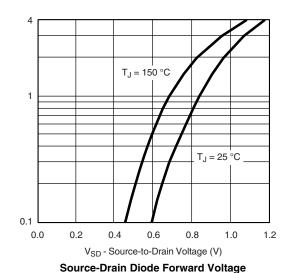


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



On-Resistance vs. Drain Current





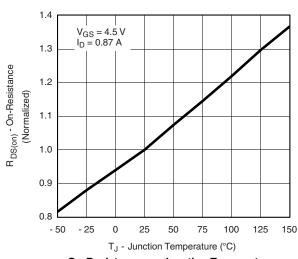
600 C_{iss}

200 C_{rss}

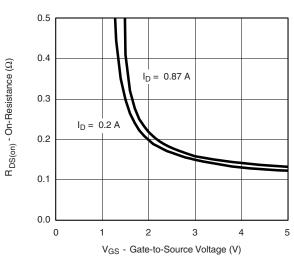
0 2 4 6 8 10 12

V_{DS} - Drain-to-Source Voltage (V)

Capacitance



On-Resistance vs. Junction Temperature



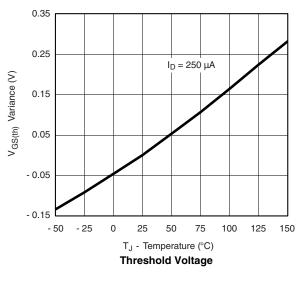
On-Resistance vs. Gate-to-Source Voltage

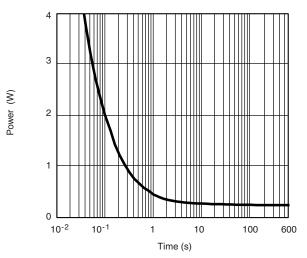
Is - Source Current (A)

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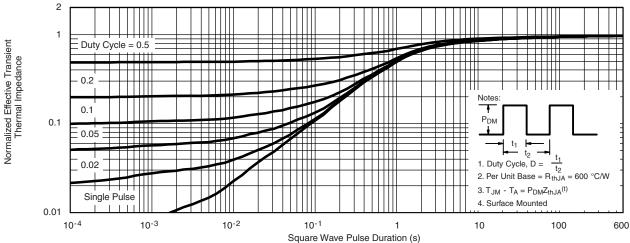
VISHAY

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

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